

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A semiconductor integrated circuit having built-in power supply circuit which, receiving an external source voltage, generates a positive voltage higher than the external source voltage and a negative voltage lower than a ground potential, the semiconductor integrated circuit comprising:

_____ a switch element connected between a first wiring for feeding ~~said the~~ negative voltage as a bias voltage for a substrate and a second wiring for supplying the ground potential.

2. (Currently Amended) The semiconductor integrated circuit according to claim 1, wherein ~~said the~~ switch element is temporarily made to conduct at ~~the a~~ time of starting up the built-in power supply circuit to set ~~the a~~ potential of the substrate, to which the negative voltage is to be applied, temporarily to the ground potential.

3. (Currently Amended) The semiconductor integrated circuit according to claim 2, further comprising:
_____ a reset circuit for generating a control signal to make ~~said the~~ switch element conduct temporarily in accordance with another control signal for starting up ~~said the~~ built-in power supply circuit.

4. (Currently Amended) The semiconductor integrated circuit according to claim 1, wherein ~~said the~~ switch element is comprised of a high voltage withstand MOSFET.

5-14 (Canceled).

15. (New) The semiconductor integrated circuit according to claim 1,

wherein the substrate is a semiconductor substrate of a first conductivity type,

wherein the semiconductor integrated circuit includes:

a first MOSFET of a first channel type having a source region of a second conductivity type different from the first conductivity type and a drain region of the second

conductivity type, both of which are formed in the semiconductor substrate of the first conductivity type.

16. (New) The semiconductor integrated circuit according to claim 15, wherein the semiconductor integrated circuit further includes:

a first well region of the second conductivity type formed in the semiconductor substrate of the first conductivity type, and

a second MOSFET of a second channel type having a source region of the first conductivity type and a drain region of the first conductivity type and a drain region of the first conductivity type, both of which are formed in the first well region.

17. (New) The semiconductor integrated circuit according to claim 16, wherein the semiconductor integrated circuit further includes:

a second well region of the second conductivity type formed in the semiconductor substrate of the first conductivity type,

a third MOSFET of the second channel type having a source region of the first conductivity type and a drain region of the first conductivity type, both of which are formed in the third well region,

a third well region of the first conductivity type formed in the second well region, and

a forth MOSFET of the first channel type having a source region of the second conductivity type and a drain region of the second conductivity type, both of which are formed in the third well region.